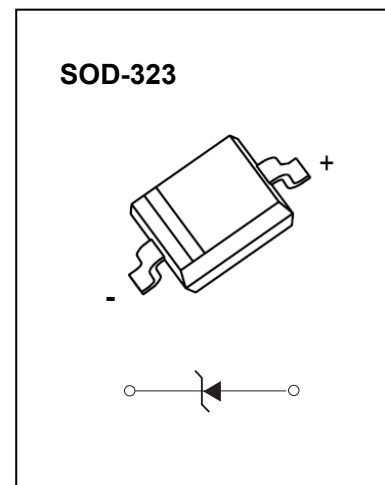


SOD-323 Plastic-Encapsulate Diodes

FEATURES

- Planar die construction
- 200mW power dissipation on ceramic PBC
- General purpose, medium current
- Ideally suited for automated assembly processes
- Available in lead free version



Marking:



XX= Device code, see table on page2 the marking code

The marking bar indicates the cathode

Maximum Ratings (T_a=25°C unless otherwise specified)

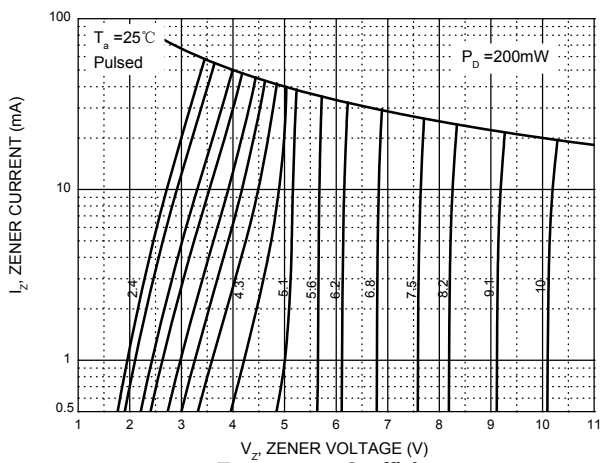
Characteristic	Symbol	Value	Unit
Forward Voltage (Note 2) @ I _F = 10mA	V _F	0.9	V
Power Dissipation(Note 1)	P _D	200	mW
Thermal Resistance from Junction to Ambient	R _{θJA}	625	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55~+150	°C

T_a=25°C unless otherwise specified

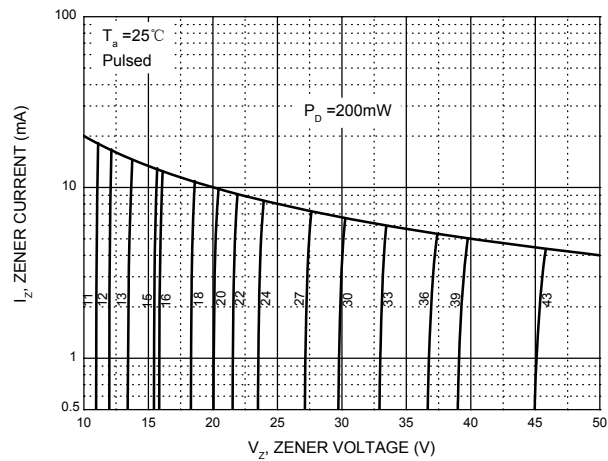
TYPE	Marking	Zener Voltage Range (Note 2)				Maximum Zener Impedance (Note 3)			Maximum Reverse Current (Note 2)		Typical Temperature Coefficient @I _{ZTC} mV/°C		Test Current I _{ZTC}
		V _Z @I _{ZT}			I _{ZT}	Z _{ZT} @I _{ZT}	Z _{ZK} @I _{ZK}	I _{ZK}	I _R	V _R			
		Nom(V)	Min(V)	Max(V)	(mA)	Ω		(mA)	μA	V	Min	Max	mA
TKBZT52C2V4S	WX	2.4	2.20	2.60	5	100	600	1.0	50	1.0	-3.5	0	5
TKBZT52C2V7S	W1	2.7	2.5	2.9	5	100	600	1.0	20	1.0	-3.5	0	5
TKBZT52C3V0S	W2	3.0	2.8	3.2	5	95	600	1.0	10	1.0	-3.5	0	5
TKBZT52C3V3S	W3	3.3	3.1	3.5	5	95	600	1.0	5	1.0	-3.5	0	5
TKBZT52C3V6S	W4	3.6	3.4	3.8	5	90	600	1.0	5	1.0	-3.5	0	5
TKBZT52C3V9S	W5	3.9	3.7	4.1	5	90	600	1.0	3	1.0	-3.5	0	5
TKBZT52C4V3S	W6	4.3	4.0	4.6	5	90	600	1.0	3	1.0	-3.5	0	5
TKBZT52C4V7S	W7	4.7	4.4	5.0	5	80	500	1.0	3	2.0	-3.5	0.2	5
TKBZT52C5V1S	W8	5.1	4.8	5.4	5	60	480	1.0	2	2.0	-2.7	1.2	5
TKBZT52C5V6S	W9	5.6	5.2	6.0	5	40	400	1.0	1	2.0	-2	2.5	5
TKBZT52C6V2S	WA	6.2	5.8	6.6	5	10	150	1.0	3	4.0	0.4	3.7	5
TKBZT52C6V8S	WB	6.8	6.4	7.2	5	15	80	1.0	2	4.0	1.2	4.5	5
TKBZT52C7V5S	WC	7.5	7.0	7.9	5	15	80	1.0	1	5.0	2.5	5.3	5
TKBZT52C8V2S	WD	8.2	7.7	8.7	5	15	80	1.0	0.7	5.0	3.2	6.2	5
TKBZT52C9V1S	WE	9.1	8.5	9.6	5	15	100	1.0	0.5	6.0	3.8	7.0	5
TKBZT52C10S	WF	10	9.4	10.6	5	20	150	1.0	0.2	7.0	4.5	8.0	5
TKBZT52C11S	WG	11	10.4	11.6	5	20	150	1.0	0.1	8.0	5.4	9.0	5
TKBZT52C12S	WH	12	11.4	12.7	5	25	150	1.0	0.1	8.0	6.0	10.0	5
TKBZT52C13S	WI	13	12.4	14.1	5	30	170	1.0	0.1	8.0	7.0	11.0	5
TKBZT52C15S	WJ	15	13.8	15.6	5	30	200	1.0	0.1	10.5	9.2	13	5
TKBZT52C16S	WK	16	15.3	17.1	5	40	200	1.0	0.1	11.2	10.4	14	5
TKBZT52C18S	WL	18	16.8	19.1	5	45	225	1.0	0.1	12.6	12.4	16	5
TKBZT52C20S	WM	20	18.8	21.2	5	55	225	1.0	0.1	14.0	14.4	18.0	5
TKBZT52C22S	WN	22	20.8	23.3	5	55	250	1.0	0.1	15.4	16.4	20.0	5
TKBZT52C24S	WO	24	22.8	25.6	5	70	250	1.0	0.1	16.8	18.4	22.0	5
TKBZT52C27S	WP	27	25.1	28.9	2	80	300	0.5	0.1	18.9	21.4	25.3	2
TKBZT52C30S	WQ	30	28.0	32.0	2	80	300	0.5	0.1	21.0	24.4	29.4	2
TKBZT52C33S	WR	33	31.0	35.0	2	80	325	0.5	0.1	23.1	27.4	33.4	2
TKBZT52C36S	WS	36	34.0	38.0	2	90	350	0.5	0.1	25.2	30.4	37.4	2
TKBZT52C39S	WT	39	37.0	41.0	2	130	350	0.5	0.1	27.3	33.4	41.2	2
TKBZT52C43S	WU	43	40.0	46.0	2	100	700	1	0.1	32	10	12	5

Notes: 1. Device mounted on ceramic PCB: 7.6mm x 9.4mm x 0.87mm with pad areas 25mm².
2. Short duration test pulse used to minimize self-heating effect.
3. f = 1kHz.

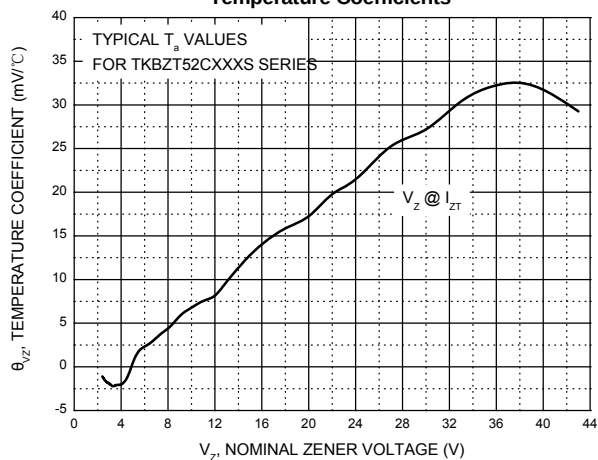
Zener Characteristics (V_z Up to 10 V)



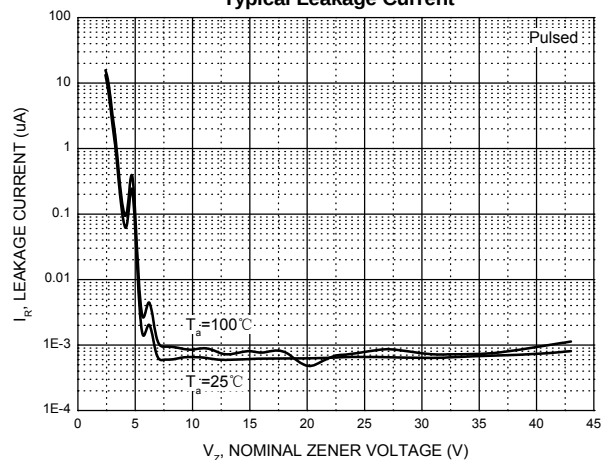
Zener Characteristics (11 V to 43 V)



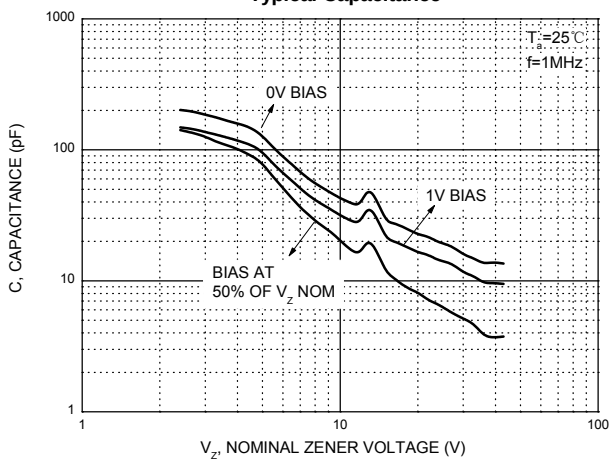
Temperature Coefficients



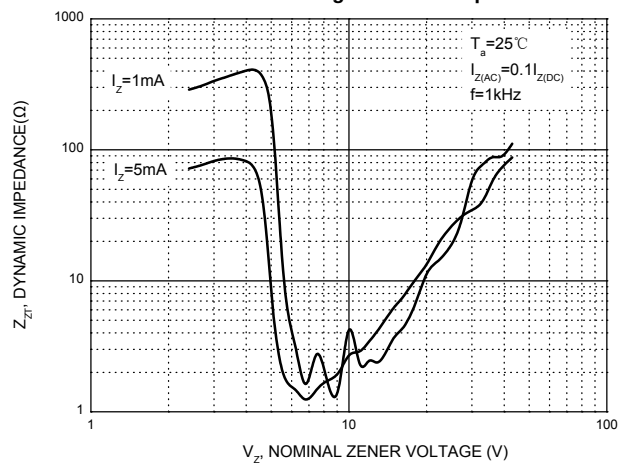
Typical Leakage Current



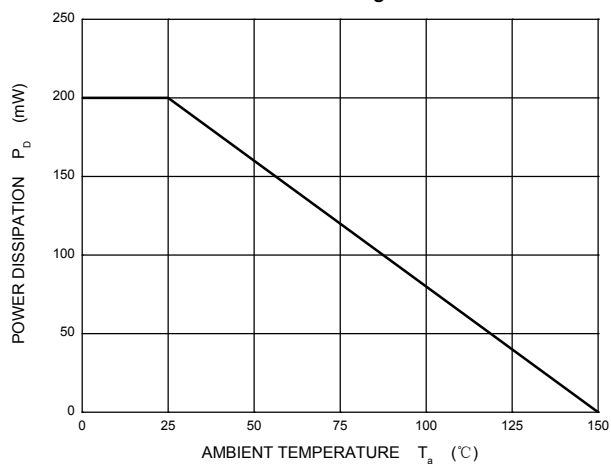
Typical Capacitance

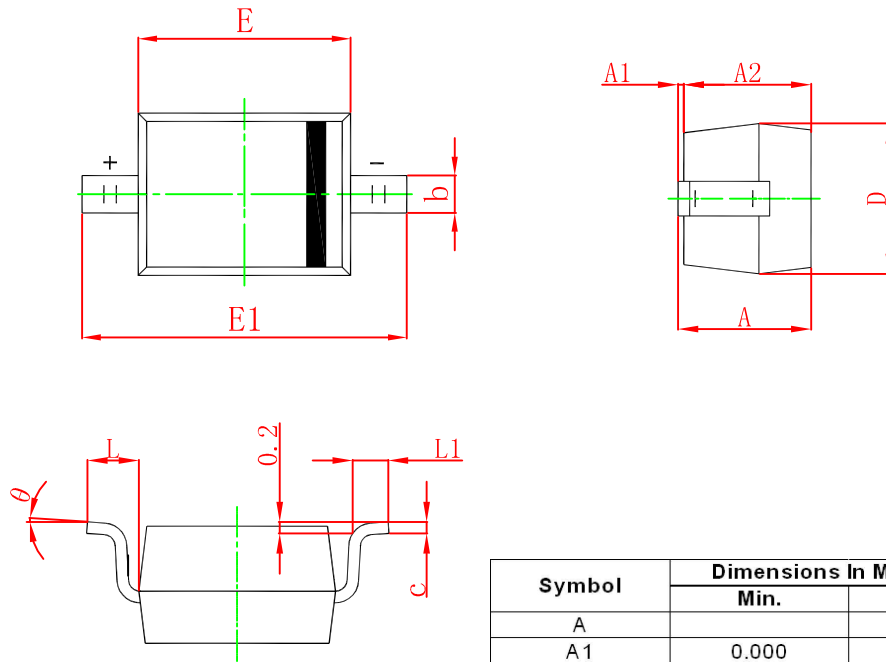


Effect of Zener Voltage on Zener Impedance



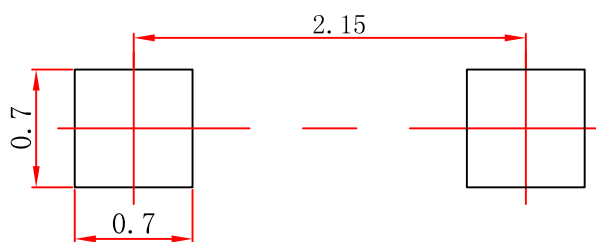
Power Derating Curve





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A		1.000		0.039
A1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.475 REF.		0.019 REF.	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

SOD-323 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.